

a 2005 0253

The invention relates to the semiconductor materials and may be used for obtaining alloys semiconductor.

Summary of the invention, according to the first variant, consists in that the alloy is made on base of Bi doped with Te and burnt up to recrystallization, the temperature gradient of which is oriented along the trigonal axis of the crystal lattice of the alloy, where Te is contained in the proportion of 1.35... 1.45 at.%, and according to the second variant, the alloy temperature gradient is oriented along the bisectrix of its crystal lattice, where Te is contained in the proportion of 1.05... 1.15 at. %.

Claims: 2

Fig.: 1